

ABSTRACT OF THE DISCLOSURE

A wafer packaging process of packaging light-emitting diode is described. A first photoresist layer is coated on an uncut wafer having a plurality of pads. The first photoresist layer is etched to form a plurality of first openings until a portion of the pad
5 within the first openings are exposed. An electroplating process is performed to fill a conductive material in the first openings to form a plurality of conductive plugs electrically connecting with the pads. A second photoresist layer is coated on a surface of the first photoresist layer. The second photoresist layer is etched to form a plurality of second openings until a portion of said conductive plugs is exposed within the second
10 openings. The second openings are filled with a conductive resilient element. Then an electroplating process is performed. Finally, the wafer is cut to form a plurality of packaged light emitting diodes.